

Abstract of the Disclosure:

A semiconductor memory device includes first and second voltage sources that have at least one different charging characteristic from each other, and performs first and second cycles each of which comprises steps of charging the signal by the first voltage source, switching from the first voltage source to the second voltage source, and charging the signal by the second voltage source after the switching step. At least one of a first time period, for which the first voltage source charges the signal, and a second time period, for which the second voltage source charges the signal, in the first cycle is different from that/those in the second cycle.